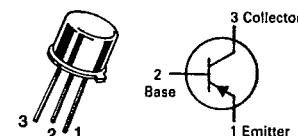


MM5005 thru MM5007

CASE 79-04, STYLE 1
TO-39 (TO-205AD)



AUDIO TRANSISTORS

PNP SILICON

MAXIMUM RATINGS

Rating	Symbol	MM5005	MM5006	MM5007	Unit
Collector-Emitter Voltage	V _{CEO}	60	80	100	Vdc
Collector-Base Voltage	V _{CBO}	80	100	120	Vdc
Emitter-Base Voltage	V _{EBO}		5.0		Vdc
Collector Current — Continuous	I _C		2.0		Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D		1.5 8.57		Watts mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D		8.0 45.7		Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +200			°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	60 80 100	— — —	Vdc
Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	V _{(BR)CBO}	80 100 120	— — —	Vdc
Emitter-Base Breakdown Voltage (I _E = 100 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current (V _{CB} = 60 Vdc, I _E = 0) (V _{CB} = 80 Vdc, I _E = 0) (V _{CB} = 100 Vdc, I _E = 0)	I _{CBO}	— — —	200 200 200	nAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	—	100	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = 1.0 mAdc, V _{CE} = 1.0 Vdc) (I _C = 150 mAdc, V _{CE} = 2.5 Vdc) (I _C = 200 mAdc, V _{CE} = 2.5 Vdc) (I _C = 250 mAdc, V _{CE} = 2.5 Vdc)	All Types MM5005 MM5006 MM5007	h _{FE}	40 50 50 50	— 250 250 250	—
Collector-Emitter Saturation Voltage (I _C = 150 mAdc, I _B = 15 mAdc)	V _{CE(sat)}	—	0.5	Vdc	
Base-Emitter On Voltage (I _C = 150 mAdc, V _{CE} = 2.5 Vdc)	V _{BE(on)}	0.65	0.8	Vdc	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain Bandwidth Product(1) (I _C = 50 mAdc, V _{CE} = 10 Vdc, f = 20 MHz)	f _T	30	—	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 100 kHz)	C _{obo}	—	20	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.